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## Features

- Supply-voltage Range: 2.7 V to 5.5 V
- Single-ended Output, no Balun Required
- Single-ended Input for RF and LO
- Excellent Isolation Characteristics
- Power-down Mode
- IP3 and Compression Point Programmable
- 2.5-GHz Operating Frequency


## Benefits

- Reduced System Costs as only Few External Component (no Balun) are Required
- Small Package
- Very Low Current Consumption
- Easy to Use

Electrostatic sensitive device.
Observe precautions for handling.


## $2.5-\mathrm{GHz}$

## Description

The U2795B is a $2.5-\mathrm{GHz}$ mixer for WLAN and RF telecommunications equipment, e.g., DECT and PCN. The IC is manufactured using Atmel's advanced bipolar technology. A double-balanced approach was chosen to assure good isolation characteristics and a minimum of spurious products. The input and output are single-ended, and their characteristics are programmable. No output transformer or balun is required.

Figure 1. Block Diagram


## Pin Configuration

Figure 2．Pinning


## Pin Description

| Pin | Symbol | Function |
| :---: | :---: | :--- |
| 1 | VS | Supply voltage |
| 2 | RFI | RF input |
| 3 | P | Programming port IP3，CP |
| 4 | SO | Output symmetry |
| 5 | IFO | IF output |
| 6 | GND | Ground |
| 7 | LOI | LO input |
| 8 | PU | Power－up |

## Functional Description

Supply Voltage

## Input Impedance

## 3rd Order Intercept Point (IP3)

The IC is designed for a supply-voltage range of 2.7 V to 5.5 V . As the IC is internally stabilized, the performance of the circuit is nearly independent of the supply voltage.

The input impedance, $\mathrm{Z}_{\mathrm{RF}}$, is about $700 \Omega$ with an additional capacitive component. This condition provides the best noise figure in combination with a matching network.

The voltage divider, $R_{P} / R_{1}$, determinates both the input and output intercept point, IIP3 and OIP3. If the value of $R_{p}$ is infinite, the maximum value of IIP3 reach about -4 dBm . The IP3/R $R_{P}$ characteristics are shown in Figure 3 and Figure 4.

Output Impedance and Intercept Point

The output impedance is shown in Figure 11 on page 8. Both low output impedance and a high intercept point are defined to a high value of $R_{P}$.

## Current Consumption, $\mathrm{I}_{\mathrm{s}}$

## Power-up

## Output Symmetry

Depending on the chosen input and output conditions of the IC, the current consumption, $I_{S}$, is between 4 mA and 10 mA . The current consumption in dependence of $R_{P}$ is shown in Figure 6 on page 6.

This feature provides extended battery lifetime. If this function is not used, pin 8 has to be connected to $\mathrm{V}_{\mathrm{S}}(\operatorname{pin} 1)$.

The symmetry of the load current can be matched and thus optimized for a given load impedance.

## Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

| Parameters | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Supply voltage | $\mathrm{V}_{\mathrm{S}}$ | 6 | V |
| Input voltage | $\mathrm{V}_{\mathrm{I}}$ | 0 to $\mathrm{V}_{\mathrm{S}}$ | V |
| Junction temperature | $\mathrm{T}_{\mathrm{j}}$ | 125 | ${ }^{\circ} \mathrm{C}$ |
| Storage-temperature range | $\mathrm{T}_{\text {stg }}$ | -40 to +125 | ${ }^{\circ} \mathrm{C}$ |

## Thermal Resistance

| Parameters | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Junction ambient SO8 | $\mathrm{R}_{\mathrm{thJA}}$ | 175 | K/W |

## Operating Range

| Parameters | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Supply-voltage range | $\mathrm{V}_{\mathrm{S}}$ | 2.7 to 5.5 | V |
| Ambient-temperature range | $\mathrm{T}_{\mathrm{amb}}$ | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |

Electrical Characteristics
$\mathrm{V}_{\mathrm{S}}=3 \mathrm{~V}, \mathrm{f}_{\mathrm{LOi}}=1 \mathrm{GHz}$, IF $=900 \mathrm{MHz}, \mathrm{RF}=100 \mathrm{MHz}, \mathrm{R}_{\mathrm{P}}=\infty$, system impedance $\mathrm{Zo}=50 \Omega, \mathrm{~T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}, \mathrm{R}_{\mathrm{T}}=56 \Omega$
reference point pin 6, unless otherwise specified

| No. | Parameters | Test Conditions | Pin | Symbol | Min. | Typ. | Max. | Unit | Type* |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1.1 | Supply voltage range |  | 1 | $\mathrm{V}_{\text {S }}$ | 2.7 |  | 5.5 | V | A |
| 1.2 | Supply Current | $\mathrm{V}_{\mathrm{S}}=2.7 \mathrm{~V}, \mathrm{R}_{\mathrm{P}}=10 \mathrm{k} \Omega$ | 1 | $\mathrm{I}_{\text {S }}$ | 9 |  | 13 | mA | A |
|  |  | $\mathrm{V}_{\mathrm{S}}=3.0 \mathrm{~V}, \mathrm{R}_{\mathrm{P}}=\infty$ | 1 | $\mathrm{I}_{\mathrm{S}}$ | 3 |  | 6.2 | mA | A |
| 1.3 | Conversion Power Gain | $\begin{aligned} & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{R}_{\mathrm{T}}=\infty \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{R}_{\mathrm{T}}=56 \Omega \end{aligned}$ | 1 | $\begin{aligned} & \mathrm{PG}_{\mathrm{C}} \\ & \mathrm{PG}_{\mathrm{C}} \end{aligned}$ |  | $\begin{aligned} & 9 \\ & 4 \end{aligned}$ |  | $\begin{aligned} & \mathrm{dB} \\ & \mathrm{~dB} \end{aligned}$ | B |
| 2 | Operating Frequencies |  |  |  |  |  |  |  |  |
| 2.1 | RF ${ }_{\text {i }}$ frequency |  | 2 | $\mathrm{RF}_{\mathrm{i}}$ | 10 |  | 2500 | MHz | D |
| 2.2 | $\mathrm{LO}_{\mathrm{i}}$ frequency |  | 7 | $\mathrm{f}_{\text {LOi }}$ | 50 |  | 2500 | MHz | D |
| 2.3 | $1 F_{0}$ frequency |  | 5 | $\mathrm{f}_{\text {IFo }}$ | 50 |  | 2500 | MHz | D |
| 3 | Isolation |  |  |  |  |  |  |  |  |
| 3.1 | LO spurious at $\mathrm{R}_{\text {Fi }}$ | $P_{\text {iLO }}=-10$ to 0 dBm | 7, 2 | $\mathrm{IS}_{\text {LO-RF }}$ |  | -30 |  | dBm | D |
| 3.2 | $\mathrm{RF}_{\mathrm{i}}$ to $\mathrm{LO}_{i}$ | $\mathrm{P}_{\mathrm{iRF}}=-25 \mathrm{dBm}$ | 2,7 | $\mathrm{IS}_{\text {RF-LO }}$ |  | 35 |  | dB | D |
| 3.3 | LO spurious at $\mathrm{IF}_{\text {。 }}$ | $P_{\text {iLO }}=-10$ to 0 dBm | 5,7 | $\mathrm{IS}_{\text {LO-IF }}$ |  | -25 |  | dBm | D |
| 3.4 | $\mathrm{IF}_{0}$ to $\mathrm{LO}_{i}$ |  | 5,7 | $\mathrm{IS}_{\text {IF-LO }}$ |  | 30 |  | dB | D |
| 4 | Output (IF) |  |  |  |  |  |  |  |  |
| 4.1 | Output compression point |  | 5 | $\mathrm{CP}_{0}$ |  | -10 |  | dBm | D |
| 5 | Input (RF) |  |  |  |  |  |  |  |  |
| 5.1 | Input impedance |  | 2 | $\mathrm{Z}_{\mathrm{RFi}}$ |  | 700\|| 0.8 |  | $\Omega \mid \mathrm{pF}$ | D |
| 5.2 | Input compression point |  | 2 | $\mathrm{CP}_{\mathrm{i}}$ |  | -14 |  | dBm | D |
| 5.3 | 3rd-order input intercept point |  | 2 | IIP3 |  | -4 |  | dBm | D |
| 6 | Input (LO) |  |  |  |  |  |  |  |  |
| 6.1 | LO level |  | 7 | $\mathrm{P}_{\text {iLO }}$ |  | -6 |  | dBm | D |
| 7 | Voltage Standing Wave Ratio (VSWR) |  |  |  |  |  |  |  |  |
| 7.1 | Input LO |  | 7 | $\mathrm{VSWR}_{\text {LOi }}$ |  | $<2$ |  |  | D |
| 7.2 | Output IF |  | 4 | $\mathrm{VSWR}_{\text {IFo }}$ |  | <2 |  |  | D |
| 8 | Noise Performance |  |  |  |  |  |  |  |  |
| 8.1 | Noise figure | $\mathrm{P}_{\mathrm{iLO}}=0 \mathrm{dBm}, \mathrm{R}_{\mathrm{T}}=\infty$ |  | NF |  | 10 |  | dB | D |
| 9 | Power-down Mode |  |  |  |  |  |  |  |  |
| 9.1 | Supply current | $\begin{aligned} & \mathrm{V}_{\mathrm{PU}}<0.5 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{PU}}=0 \mathrm{~V} \end{aligned}$ | 1 | $\mathrm{I}_{\text {SPU }}$ |  | $<5$ | 30 | $\begin{aligned} & \mu \mathrm{A} \\ & \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline B \\ & B \end{aligned}$ |
| 10 | Power-down Voltage |  |  |  |  |  |  |  |  |
| 10.1 | "Power ON" | $\begin{aligned} & \mathrm{V}_{\mathrm{S}}=3.5 \text { to } 5.5 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{S}}=2.7 \text { to } 3.5 \mathrm{~V} \end{aligned}$ | 8 | $\mathrm{V}_{\text {PON }}$ | $\begin{gathered} \mathrm{V}_{\mathrm{S}}-0.5 \\ \mathrm{~V}_{\mathrm{S}} \end{gathered}$ |  | $\begin{aligned} & \mathrm{V}_{\mathrm{S}}+0.5 \\ & \mathrm{~V}_{\mathrm{S}}+0.5 \end{aligned}$ | $\begin{aligned} & \mathrm{V} \\ & \mathrm{~V} \end{aligned}$ | $\begin{aligned} & \mathrm{D} \\ & \mathrm{D} \end{aligned}$ |
| 10.2 | "Power DOWN" |  | 8 | $\mathrm{V}_{\text {PDN }}$ |  |  | 1 | V | D |
| 10.3 | Power-down current | Power ON Power DOWN | 8 | $I_{\text {PON }}$ <br> IPDN |  | $\begin{gathered} 0.15 \\ <5 \end{gathered}$ | 0.22 | $\begin{aligned} & \mathrm{mA} \\ & \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \text { A } \\ & \text { D } \end{aligned}$ |
| 10.4 | Settling time |  | 5,8 | $\mathrm{t}_{\text {sPD }}$ |  | < 30 |  | $\mu \mathrm{s}$ | D |

${ }^{*}$ ) Type means: $A=100 \%$ tested, $B=100 \%$ correlation tested, $C=$ Characterized on samples, $D=$ Design parameter

Figure 3. IIP3 versus Resistor $\mathrm{R}_{\mathrm{p}}$, IF: 900 MHz


Figure 4. OIP3 versus Resistor $\mathrm{R}_{\mathrm{p}}$, IF: 900 MHz


Figure 5. Gain versus Resistor $R_{p}$, LO: 1030 MHz , level -10 dBm ; RF: 130 MHz , $-30 \mathrm{dBm}, \mathrm{R}_{\mathrm{T}}=56 \Omega$


Figure 6. Supply Current $\mathrm{I}_{\mathrm{S}}$ versus Resistor $\mathrm{R}_{\mathrm{p}}$


Figure 7. Gain versus IF Output Frequency, LO Level: -6 dBm, RF: $130 \mathrm{MHz},-35 \mathrm{dBm}$; Parameter: RF Input Termination


Figure 8. IIP3 versus IF Output Frequency, LO Level: -6 dBm; RF: $130 \mathrm{MHz} /$ $130.1 \mathrm{MHz},-35 \mathrm{dBm}$; Parameter: RF Input Termination


Figure 9. Double Sideband Noise Figure versus IF Output Frequency; LO: 1000 MHz, Level 0 dBm ; no RF Input Matching, $\mathrm{R}_{\mathrm{T}}$ Left Out


Figure 10. Typical VSWR Frequency Response of the IF Output, $\mathrm{R}_{\mathrm{P}}=\infty$


Figure 11. Typical Impedance of the Output versus $R_{P}$ at Frequency $f_{I F o}=900 \mathrm{MHz}$ Markers (from Left to Right): $R_{p}=\propto / 22 \mathrm{k} \Omega / 10 \mathrm{k} \Omega / 8.2 \mathrm{k} \Omega / 5.6 \mathrm{k} \Omega$


Figure 12. Typical S11 Frequency Response of the IF Output, $\mathrm{R}_{\mathrm{P}}=\infty$, IF Frequency from 100 MHz to 1000 MHz , Marker: 900 MHz


Figure 13. Typical S11 Frequency Response of the RF Input, $R_{P}=\infty, R_{T}=\infty$ RF Frequency from 100 MHz to 1000 MHz , Marker: 900 MHz


Figure 14. Typical S11 Frequency Response of the LO Input, $R_{P}=\infty$, LO Frequency from 100 MHz to 1000 MHz , Marker: 900 MHz


## Application



Table 1. Part List

| Part | Value |
| :---: | :---: |
| $\mathrm{C}_{1}$ | 10 nF |
| $\mathrm{C}_{2}, \mathrm{C}_{3}, \mathrm{C}_{4}, \mathrm{C}_{5}, \mathrm{C}_{6}, \mathrm{C}_{7}$ | 100 pF |
| ${ }^{*} \mathrm{R}_{\mathrm{P}}$ |  |
| ${ }^{*} \mathrm{R}_{\mathrm{SO}}$ | $50-\Omega$ Microstrip |
| $--\infty$ | $68 \Omega$ |
| $\mathrm{R}_{\mathrm{T}}$ | optional |

If the part-list values are used, the PU settling time is < $20 \mu \mathrm{~s}$. Using other values, time requirements in burst-mode applications have to be considered.
The values of $R_{S O}$ and $R_{P}$ depend on the input and output condition requirements. For $R_{\text {SO }}, 68 \Omega$ is recommended.

By means of the optional $\mathrm{R}_{1}$, the intercept and compression point can be slightly increased; values between $500 \Omega$ and $1 \mathrm{k} \Omega$ are suitable. Please note that such modification will also increase the supply current.

## Application Circuit (Evaluation Board)




Ordering Information

| Extended Type Number | Package | Remarks |
| :--- | :---: | :--- |
| U2795B-MFP | SO8 | Tube |
| U2795B-MFPG3 | SO8 | Taped and reeled |

Package Information

technical drawings according to DIN specifications

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